

CMKD4448

**SURFACE MOUNT
TRIPLE ISOLATED
HIGH SPEED SILICON
SWITCHING DIODES**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in an ULTRAmimi™ surface mount package, designed for applications requiring high speed switching applications.

MARKING CODE: K48

ULTRAmimi™



SOT-363 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R 75
 V_{RRM} 100
 I_F 250
 I_{FRM} 500
 I_{FSM} 4.0
 I_{FSM} 1.0
 P_D 325
 T_J, T_{stg} -65 to +175
 θ_{JA} 461

UNITS

V
V
mA
mA
A
A
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

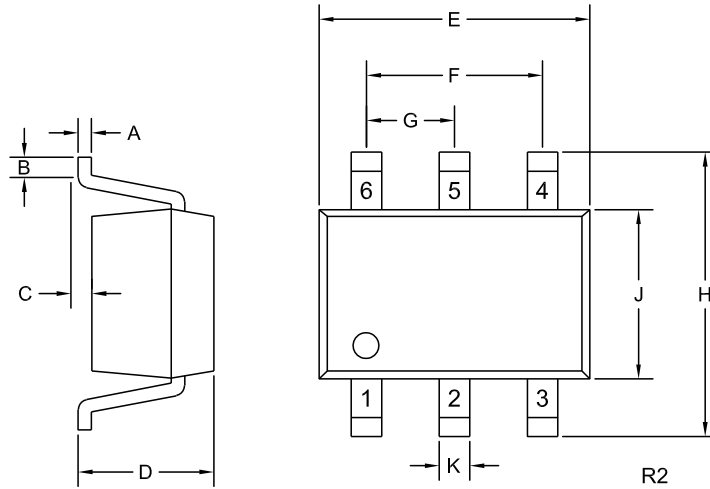
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=20\text{V}$		25	nA
BV_R	$I_R=5.0\mu\text{A}$	75		V
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1.0\text{MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		4.0	ns

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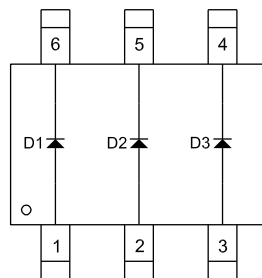
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SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

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DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R6 (19-September 2011)